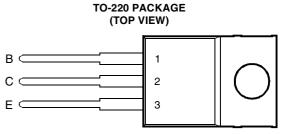
TIP31D, TIP31E, TIP31F NPN SILICON POWER TRANSISTORS

BOURNS®

- 40 W at 25°C Case Temperature
- **3 A Continuous Collector Current**
- **5 A Peak Collector Current**
- **Customer-Specified Selections Available**



Pin 2 is in electrical contact with the mounting base. MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING			VALUE	UNIT	
	TIP31D		160		
Collector-base voltage $(I_E = 0)$	TIP31E	V _{CBO}	180	V	
	TIP31F		200		
	TIP31D		120		
Collector-emitter voltage (I _B = 0)	TIP31E	V _{CEO}	140	V	
	TIP31F		160		
Emitter-base voltage			5	V	
Continuous collector current			3	A	
Peak collector current (see Note 1)			5	A	
Continuous base current			1	A	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)			40	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)			2	W	
Unclamped inductive load energy (see Note 4)			32	mJ	
Operating junction temperature range			-65 to +150	°C	
Storage temperature range			-65 to +150	°C	
Lead temperature 3.2 mm from case for 10 seconds			250	°C	

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%.$

Derate linearly to 150°C case temperature at the rate of 0.32 W/°C.
Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)} = 0.4$ A, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = 20 V$.

PRODUCT INFORMATION

TIP31D, TIP31E, TIP31F NPN SILICON POWER TRANSISTORS



electrical characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS			MIN	ТҮР	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage			TIP31D	120			
		I _C = 30 mA	I _B = 0	TIP31E	140			V
		(see Note 5)		TIP31F	160			
	Collector-emitter cut-off current	V _{CE} = 160 V	$V_{BE} = 0$	TIP31D			0.2	
I _{CES}		V _{CE} = 180 V	$V_{BE} = 0$	TIP31E		0.2	mA	
		V _{CE} = 200 V	$V_{BE} = 0$	TIP31F			0.2	
I _{CEO}	Collector cut-off current	V _{CE} = 90 V	$I_{B} = 0$				0.3	mA
	Emitter cut-off	V _{EB} = 5 V	I _C = 0				1	mA
I _{EBO}	current	VEB - SV						ША
h _{FE}	Forward current	$V_{CE} = 4 V$	I _C = 1 A	(see Notes 5 and 6)	25			
	transfer ratio	$V_{CE} = 4 V$	I _C = 3 A		5			
V _{CE(sat)}	Collector-emitter	I _B = 750 mA	$I_{\rm C} = 3 {\rm A}$ (see Notes 5 and 6	(see Notes 5 and 6)			2.5	V
- CE(sal)	saturation voltage	-B		(
V _{BE}	Base-emitter	V _{CE} = 4 V	$I_{\rm C} = 3$ A	(see Notes 5 and 6)			1.8	V
DE	voltage			(_	
h _{fe}	Small signal forward	V _{CE} = 10 V	I _C = 0.5 A	f = 1 kHz	20			
le	current transfer ratio							
h _{fe}	Small signal forward	V _{CE} = 10 V	$I_{\rm C} = 0.5 {\rm A}$ f	f = 1 MHz	3			
	current transfer ratio							

NOTES: 5. These parameters must be measured using pulse techniques, $t_0 = 300 \ \mu s$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER			ТҮР	MAX	UNIT
R _{θJC}	Junction to case thermal resistance			3.125	°C/W
R_{\thetaJA}	Junction to free air thermal resistance			62.5	°C/W

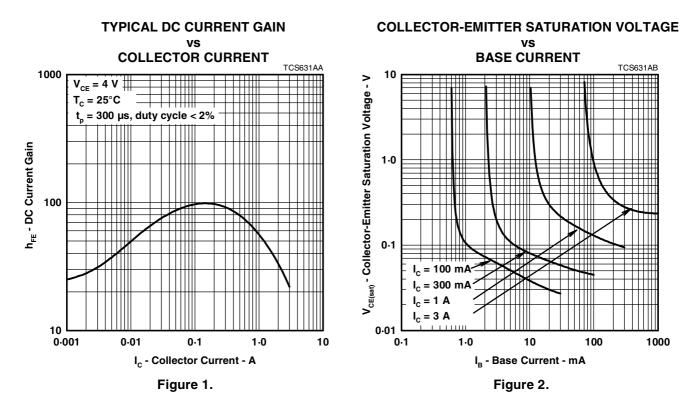
resistive-load-switching characteristics at 25°C case temperature

	PARAMETER	TEST CONDITIONS [†]			MIN	ТҮР	MAX	UNIT
t _{on}	Turn-on time	I _C = 1 A	$I_{B(on)} = 0.1 A$	$I_{B(off)} = -0.1 A$		0.5		μs
t _{off}	Turn-off time	$V_{BE(off)} = -4.3 V$	$R_L = 30 \ \Omega$	t_p = 20 µs, dc \leq 2%		2		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.



TYPICAL CHARACTERISTICS



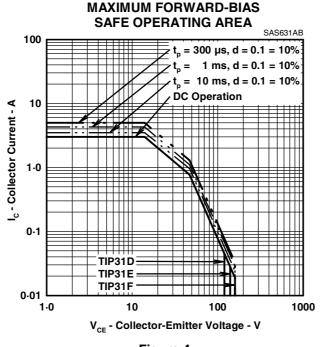
BASE-EMITTER VOLTAGE vs **COLLECTOR CURRENT** TCS631AC 1.0 $V_{CE} = 4 V$ T_c = 25°C V_{BE} - Base-Emitter Voltage - V 0.9 0.8 0.7 0.6 0.5 0.01 0.1 1.0 10 I_c - Collector Current - A Figure 3.

PRODUCT INFORMATION

AUGUST 1978 - REVISED SEPTEMBER 2002 Specifications are subject to change without notice.

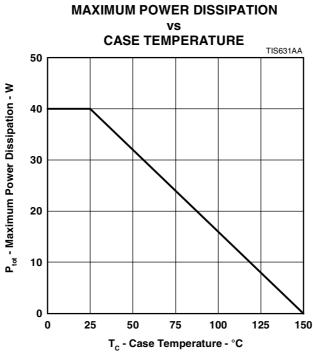
BOURNS®

MAXIMUM SAFE OPERATING REGIONS











PRODUCT INFORMATION

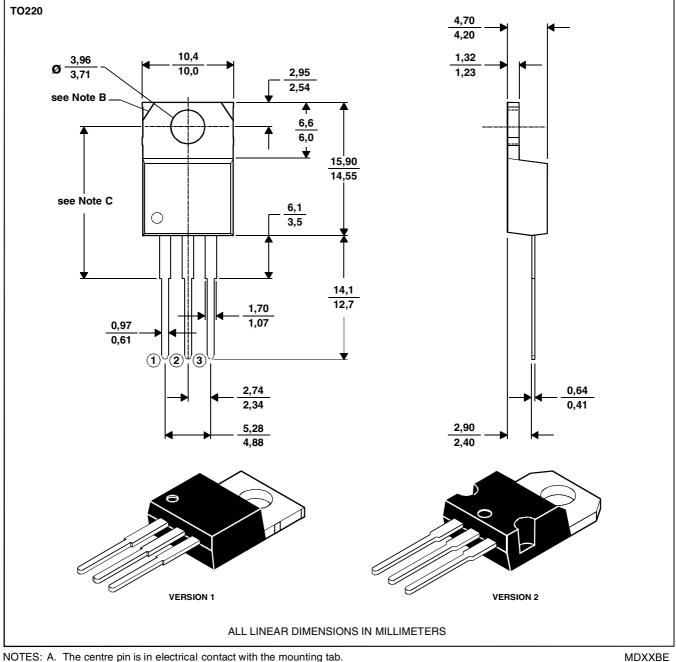
AUGUST 1978 - REVISED SEPTEMBER 2002 Specifications are subject to change without notice.

MECHANICAL DATA

TO-220

3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



B. Mounting tab corner profile according to package version.

C. Typical fixing hole centre stand off height according to package version. Version 1, 18.0 mm. Version 2, 17.6 mm.

PRODUCT INFORMATION

AUGUST 1978 - REVISED SEPTEMBER 2002 Specifications are subject to change without notice.